

0057-2533-2



IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF:

HIDEKI TAKAHASHI

: GROUP ART UNIT: 2811

SERIAL NO: 09/421,217

FILED: OCTOBER 20, 1999

: EXAMINER: LOKE, S

FOR: INSULATED GATE SEMICONDUCTOR
DEVICE AND MANUFACTURING
METHOD THEREOF

9/B
FJONES
7-26-01
RECEIVED
JUL 25 2001
TECHNOLOGY CENTER 2800

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In response to the Office Action of April 24, 2001, please amend the above-identified application as follows:

IN THE TITLE

Please amend the title to read as follows:

INSULATED GATE SEMICONDUCTOR DEVICE WITH LOW ON
VOLTAGE AND MANUFACTURING METHOD THEREOF

IN THE CLAIMS

Please amend Claim 22 as follows. A marked-up copy follows this amendment.

B1 Figs. 3, 22, 23
Sub C1
22. (Amended) An insulated gate semiconductor device, comprising:
a first semiconductor layer of a first conductivity type having first and second main
surfaces on opposite sides thereof;